

ABSTRACT OF THE DISCLOSURE

A semiconductor light-receiving device includes:
a substrate that has a first surface and a second
surface facing each other; a first semiconductor layer
5 that is formed on the first surface of the substrate
and includes at least one semiconductor layer of a
first conductivity type; a light absorption layer that
is formed on the first semiconductor layer and
generates carriers in accordance with incident light; a
10 second semiconductor layer that is formed on the light
absorption layer and includes at least one
semiconductor layer of a second conductivity type; a
first electrode part that is electrically connected to
the first semiconductor layer and applies a first
15 potential thereto; a second electrode part that is
electrically connected to the second semiconductor
layer and applies a second potential thereto; and a
third semiconductor layer of the second conductivity
type that is interposed between the first surface of
20 the substrate and the first semiconductor layer.